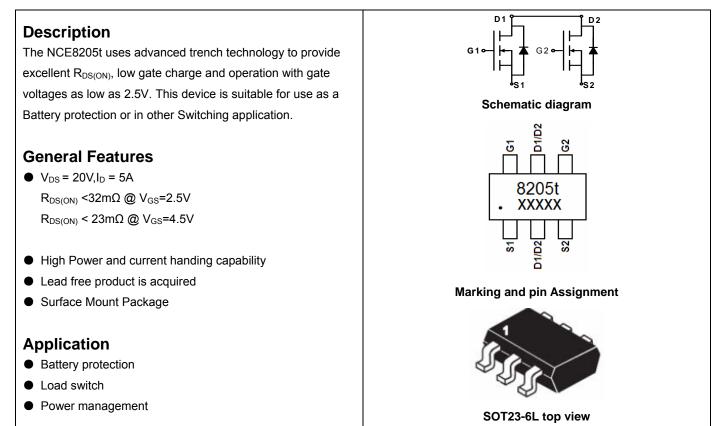


NCE N-Channel Enhancement Mode Power MOSFET



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
8205t	NCE8205t	SOT23-6L	Ø180mm	8mm	3000 units

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	20	V
Gate-Source Voltage	Vgs	±12	V
Drain Current-Continuous	Ι _D	5	А
Drain Current-Pulsed (Note 1)	I _{DM}	25	А
Maximum Power Dissipation	PD	1.25	W
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	R _{0JA}	100	°C/W

Electrical Characteristics (T_A=25[°]C unless otherwise noted)

Parameter	Symbol	OI Condition		Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	20			V



NCE8205t

Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =19.5V, V_{GS} =0V	-	-	1	μA
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±12V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	0.5	0.7	1.2	V
Drain-Source On-State Resistance		V_{GS} =4.5V, I_{D} =5A	-	16.5	23	mΩ
Dialit-Source Off-State Resistance	R _{DS(ON)}	V _{GS} =2.5V, I _D =5A	-	22	32	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =5A	-	10	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	V _{DS} =10V,V _{GS} =0V,	-	550	-	PF
Output Capacitance	C _{oss}	v _{DS} =10v,v _{GS} =0v, F=1.0MHz	-	125	-	PF
Reverse Transfer Capacitance	Crss	F = 1.00012	-	64	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	9	-	nS
Turn-on Rise Time	t _r	V_{DD} =10V,I _D =5A	-	10	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =4V, R_{GEN} =10 Ω	-	32	-	nS
Turn-Off Fall Time	t _f		-	24	-	nS
Total Gate Charge	Qg		-	9.5	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =10V,I _D =5A, V _{GS} =4.5V	-	2.1	-	nC
Gate-Drain Charge	Q _{gd}	v _{GS} -4.3v	-	1.4	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =5A	-	0.8	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	5	А

Notes:

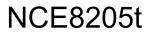
1. Repetitive Rating: Pulse width limited by maximum junction temperature.

Surface Mounted on FR4 Board, t ≤ 10 sec.
Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.

4. Guaranteed by design, not subject to production







Typical Electrical and Thermal Characteristics

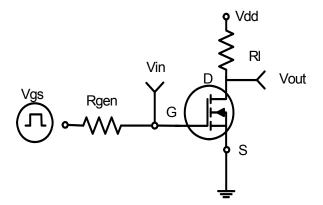
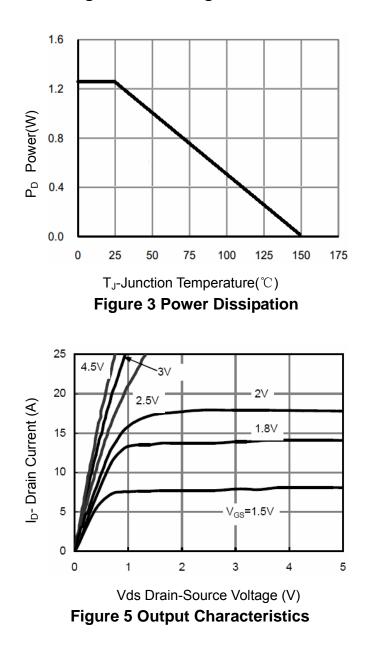
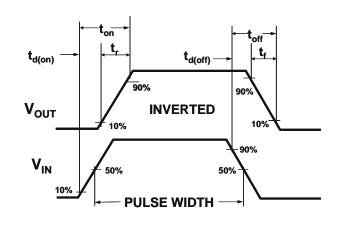


Figure 1:Switching Test Circuit







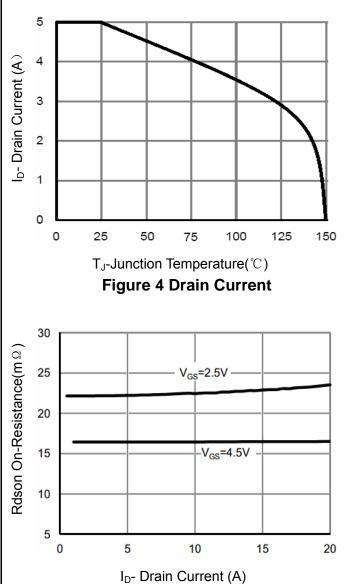
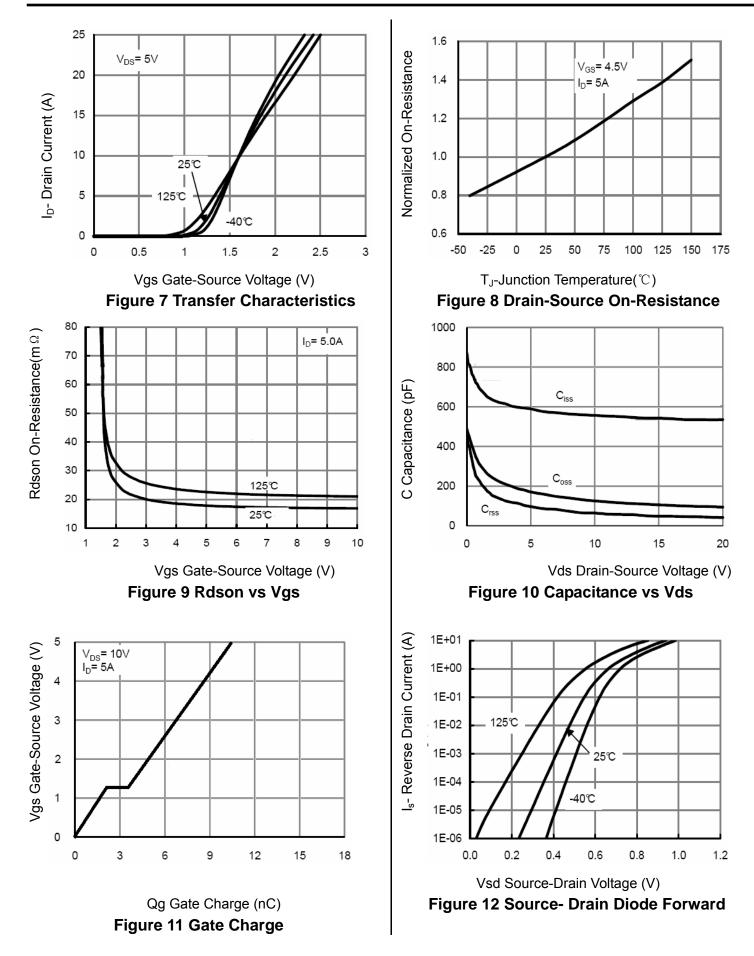


Figure 6 Drain-Source On-Resistance

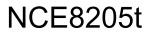


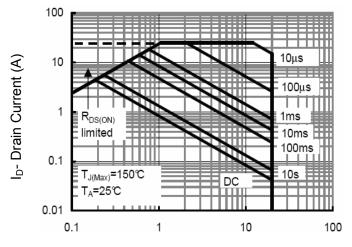
NCE8205t



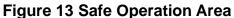








Vds Drain-Source Voltage (V)



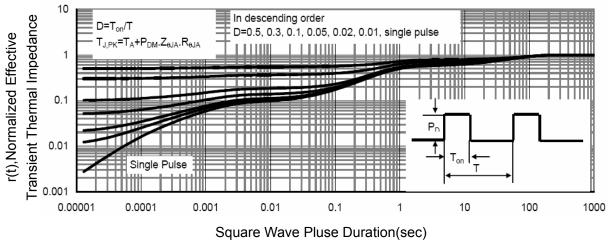


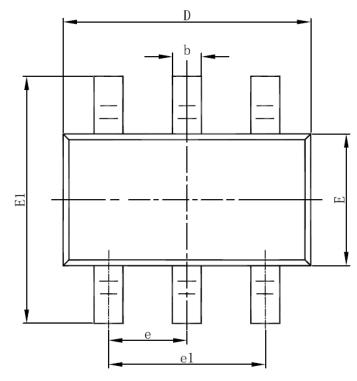
Figure 14 Normalized Maximum Transient Thermal Impedance

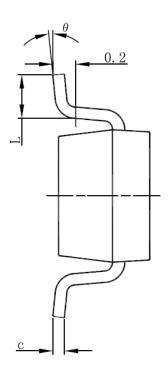


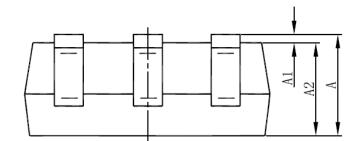
Pb Free Product

NCE8205t

SOT23-6L Package Information







Symbol	Dimensions Ir	n Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
A	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
е	0.950	(BSC)	0.037(BSC)		
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	





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